

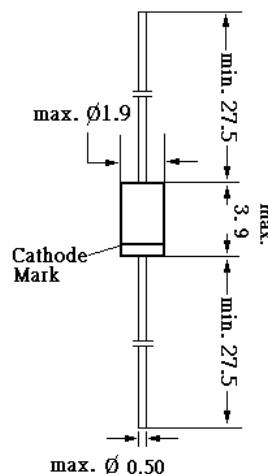
# BA282, BA283

## SILICON EPITAXIAL PLANAR DIODE SWITCHES

for electronic band-switching in radio and TV tuners in the frequency range of 50 to 1000 MHz. The dynamic forward resistance is constant and very small over a wide range of frequency and forward current. The reverse capacitance is also small and largely independent of the reverse voltage.

These diodes are delivered taped.

Details see "Taping".



Glass case JEDEC DO-35

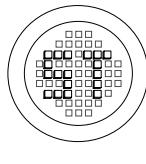
Dimensions in mm

Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

	Symbol	Value	Unit
Reverse Voltage	$V_R$	35	V
Forward Current at $T_{\text{amb}} = 25^\circ\text{C}$	$I_F$	100	mA
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_S$	-55 to +150	$^\circ\text{C}$

Characteristics at  $T_j = 25^\circ\text{C}$

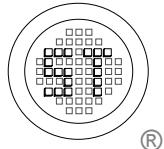
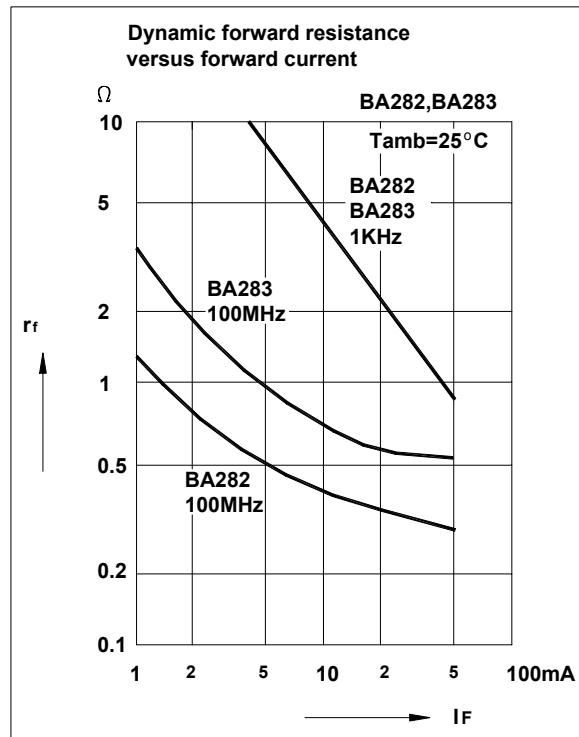
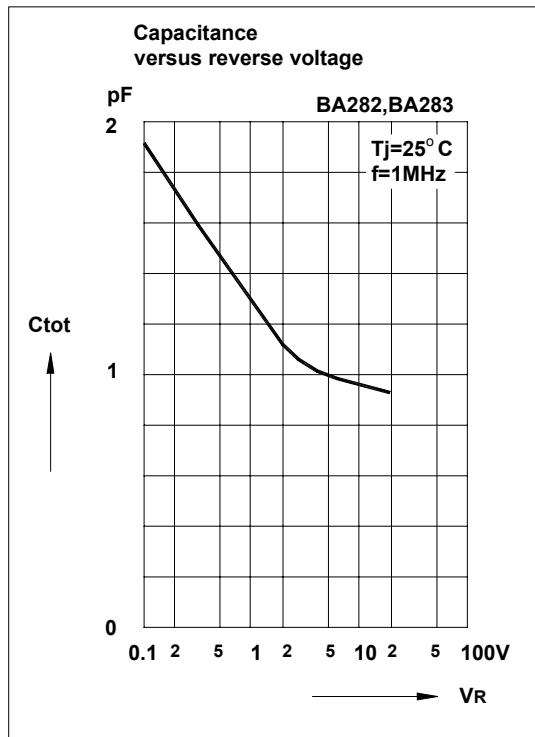
	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{mA}$	$V_F$	-	-	1	V
Leakage Current at $V_R = 20\text{V}$	$I_R$	-	-	50	nA
Dynamic Forward Resistance at $f = 50$ to $1000\text{ MHz}$ , $I_F = 3\text{mA}$	$r_f$	-	-	0.7	$\Omega$
	BA282				
	BA283				
Dynamic Forward Resistance at $f = 50$ to $1000\text{ MHz}$ , $I_F = 10\text{mA}$	$r_f$	-	-	0.5	$\Omega$
	BA282				
	BA283				
Capacitance at $V_R = 1\text{V}$ , $f = 1\text{MHz}$	$C_{\text{tot}}$	-	-	1.5	pF
at $V_R = 3\text{V}$ , $f = 1\text{MHz}$	BA282	$C_{\text{tot}}$	-	1.25	pF
	BA283	$C_{\text{tot}}$	-	1.2	pF
Series Inductance across Case	$L_S$	-	2.5	-	nH



РАДИОТЕХ-ТРЕЙД

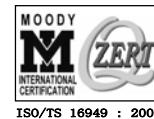
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**SEMTECH ELECTRONICS LTD.**

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002  
Certificate No. 05103



ISO 14001  
Certificate No. 7116



ISO 9001 : 2000  
Certificate No. 950-199-002-001

Dated : 31/12/2002